SAC2F100N/P80S

800V Isolation FRD Module

Features

- Repetitive Reverse Voltage: V_{RRM} = 800V
- Low Forward Voltage: V_F(typ.) = 1.5V @ I_F=100A
- Average Forward Current: $I_{F(AV)}$ = 100A @ T_C=100℃
- Reverse Recovery Time: t_{rr}(typ.) =135ns
- Extensive Characterization of Recovery Parameters
- Reduced EMI and RFI
- Isolation Type Package
- 150℃ Operating Junction Temperature
- Built-in N/P-common Dual FRD Construction

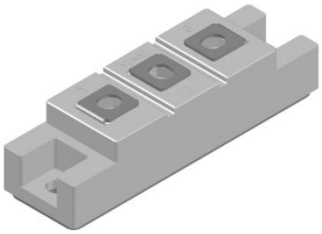
Applications

- High Speed & High Power converters, Inverter Welders
- Various Switching and Telecommunication Power Supply
- Cutting Machine

Description

The Fast Recovery Diode module devices are optimized to reduce losses and EMI/RFI in high frequency power conditioning electrical systems.
The Fast Recovery Diode module is ideally suited for power converters, inverter welders, motor drives and other applications where switching losses are significant portion of the total losses.

Package Type & Internal Circuit



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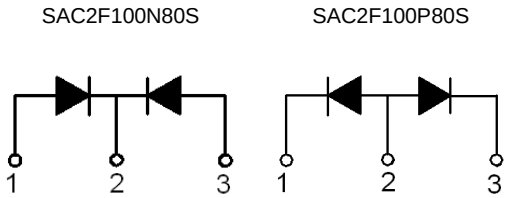


Internal Circuit

Absolute Maximum Ratings (Per diode at T_C=25 ℃ unless otherwise noted)

Symbol	Parameter		Ratings	Unit
V_{RRM}	Repetitive Peak Reverse Voltage		800	V
V_R	DC Blocking Voltage		640	V
$I_{F(AV)}$	Average Rectified Forward Current	T_C = 25℃	200	A
		T_C = 100℃	100	
I_{FSM}	Non-repetitive Peak Surge Current 60Hz Single Half-sine Wave		1750	A
I^2t	I^2t For Fusing 60Hz Sine Wave		$12.7 * 10^3$	A^2S
P_D	Maximum Power Dissipation		360	W
V_{iso}	Isolation Voltage @AC 1 Minutes		2500	V
T_J	Junction Temperature		-55 ~ +150	℃
T_{STG}	Storage Temperature Range		-55 ~ +150	℃
	Mounting Torque (M5)		4.0	N.m
	Terminal Torque (M5)		2.0	N.m
	Weight		112	g

Electrical Characteristics (Per diode @T_C=25 ℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_F	Forward Voltage Drop	I_F=100A	-	1.5	1.8	V
		I_F=100A, T_C=100℃	-	1.25	-	V
I_{RM}	Reverse Leakage Current	V_R=800V	-	-	0.5	mA
		V_R=800V, T_C=100℃	-	-	1	mA
t_{rr}	Reverse Recovery Time	I_F=1A, di/dt=-200A/us	-	35	-	ns
t_{rr}	Reverse Recovery Time	I_F=100A, di/dt=-200A/us	-	135	180	ns
I_{rr}	Reverse Recovery Current		-	15.5	-	A
t_{rr}	Reverse Recovery Time	I_F=100A, di/dt=-200A/us, T_C=100℃	-	320	-	ns
I_{rr}	Reverse Recovery Current		-	30	-	A

Thermal Characteristics

Symbol	Parameter	Ratings	Unit
$R_{th\ (J-C)}$	Thermal Resistance, Junction to case	0.34	℃/W

Typical Performance Characteristics

Fig. 1. Typical Characteristics: V_F vs. I_F

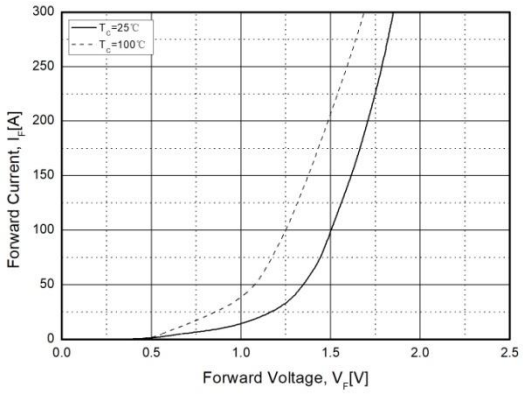


Fig. 2. Typical Reverse Recovery Time vs. di/dt

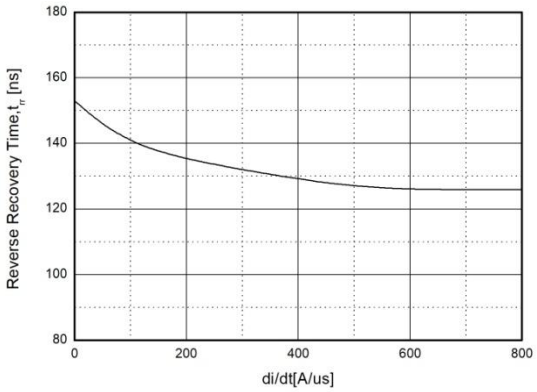


Fig. 3. Transient Thermal Impedance Characteristics ($R_{th(J-C)}$)

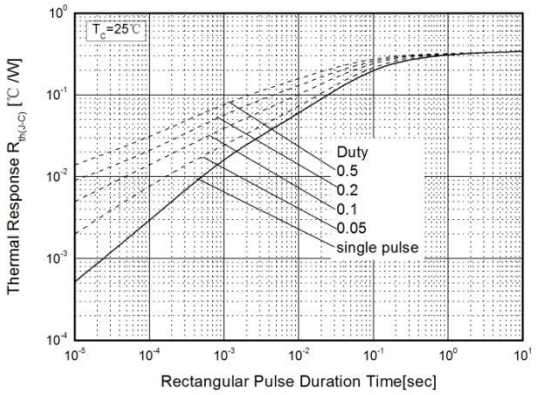
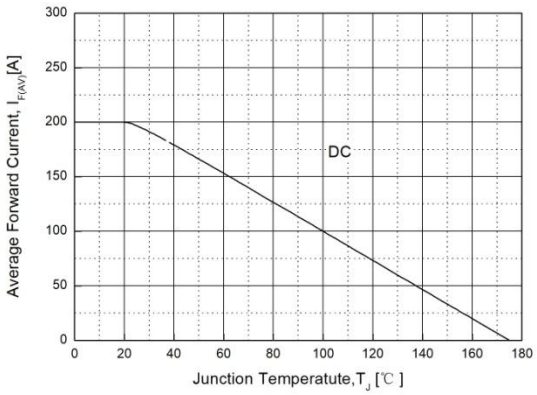


Fig. 4. Forward Current Derating Curve



Package Dimensions

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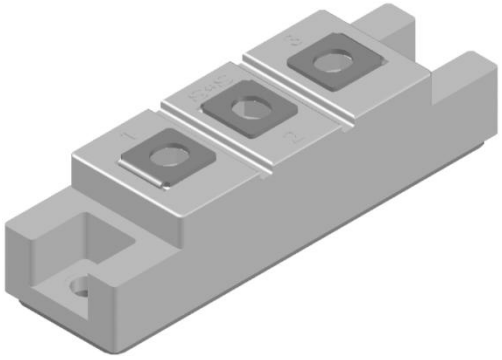
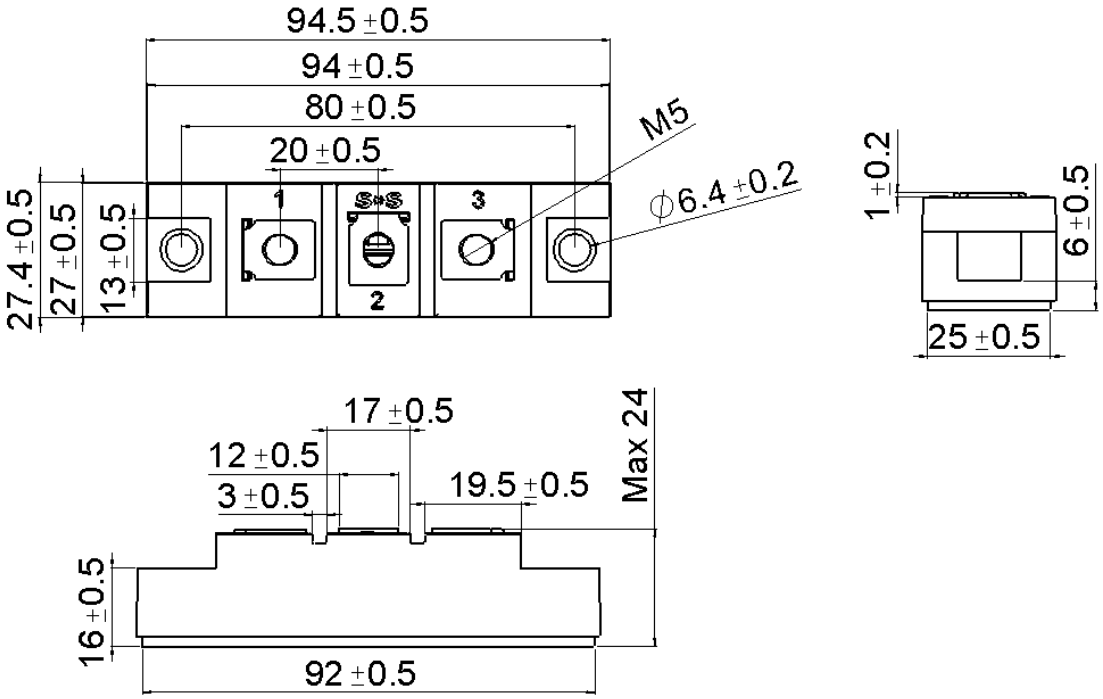


(Dimensions in Millimeters)



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